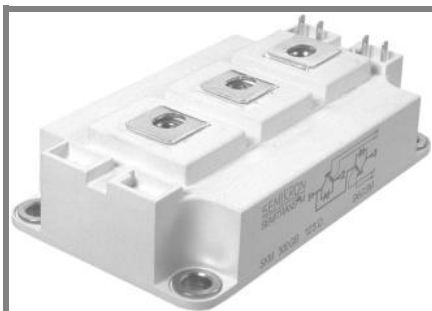


SKM 300GB12T4



SEMITRANS® 3

IGBT4 Modules

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Target Data

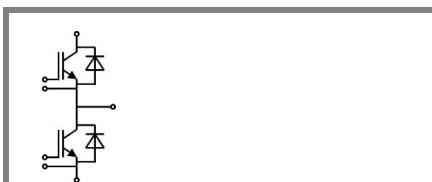
Features

- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)

Typical Applications

Remarks

- Case temperature limited to $T_C = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j \leq 150^\circ$

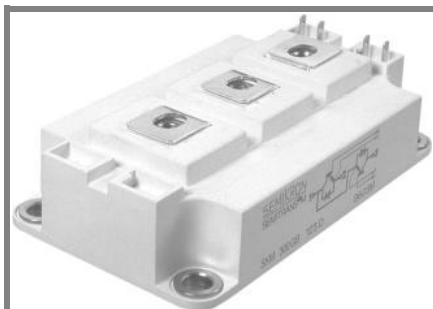


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Absolute Maximum Ratings		$T_C = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V	
I_C	$T_j = 175^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	420	A
		$T_{case} = 80^\circ\text{C}$	325	A
I_{CRM}	$I_{CRM} = 3 \times I_{CNOM}$	900	A	
V_{GES}		± 20	V	
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10	μs	
Inverse Diode				
I_F	$T_j = 175^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	350	A
		$T_{case} = 80^\circ\text{C}$	260	A
I_{FRM}	$I_{FRM} = 3 \times I_{FNOM}$	900	A	
I_{FSM}	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 175^\circ\text{C}$	1720	A
Module				
$I_{t(RMS)}$		500	A	
T_{vj}		$-40 \dots +175$	$^\circ\text{C}$	
T_{stg}		$-40 \dots +125$	$^\circ\text{C}$	
V_{isol}	AC, 1 min.	4000	V	

Characteristics		$T_C = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 12\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25^\circ\text{C}$			mA
		$T_j = 150^\circ\text{C}$			
V_{CE0}		$T_j = 25^\circ\text{C}$	0,8	0,9	V
		$T_j = 150^\circ\text{C}$	0,7	0,8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	3,5	3,8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	5,2	5,5	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 300\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,85	2,05	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	2,25	2,45	V
C_{res}	$V_{CE} = , V_{GE} = \text{V}$	$f = \text{MHz}$	18,6		nF
C_{oes}			1,2		nF
C_{res}			1		nF
Q_G	$V_{GE} = -8\text{ V} / +15\text{ V}$		1700		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		2,5		Ω
$t_{d(on)}$	$R_{Gon} = \Omega$	$V_{CC} = 600\text{ V}$ $I_{Cnom} = 300\text{ A}$ $T_j = 150^\circ\text{C}$ $V_{GE} = -\pm 15\text{ V}$	33		ns
t_r					ns
E_{on}	$R_{Goff} = \Omega$		33		mJ
$t_{d(off)}$					ns
t_f					ns
E_{off}			33		mJ
$R_{th(j-c)}$					per IGBT

SKM 300GB12T4



SEMITRANS® 3

IGBT4 Modules

SKM 300GB12T4

Target Data

Features

- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)

Typical Applications

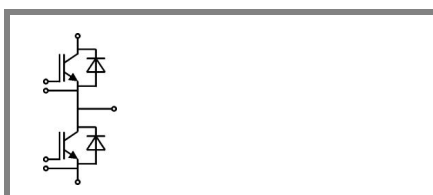
Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j \leq 150^\circ$

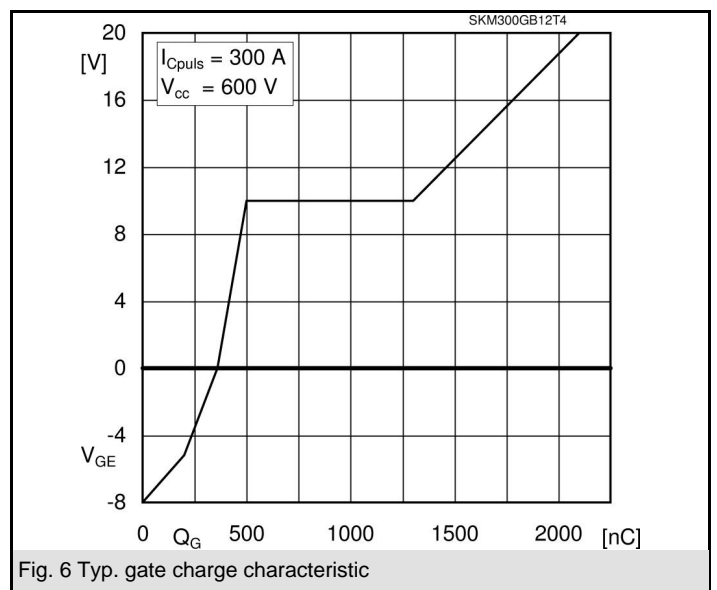
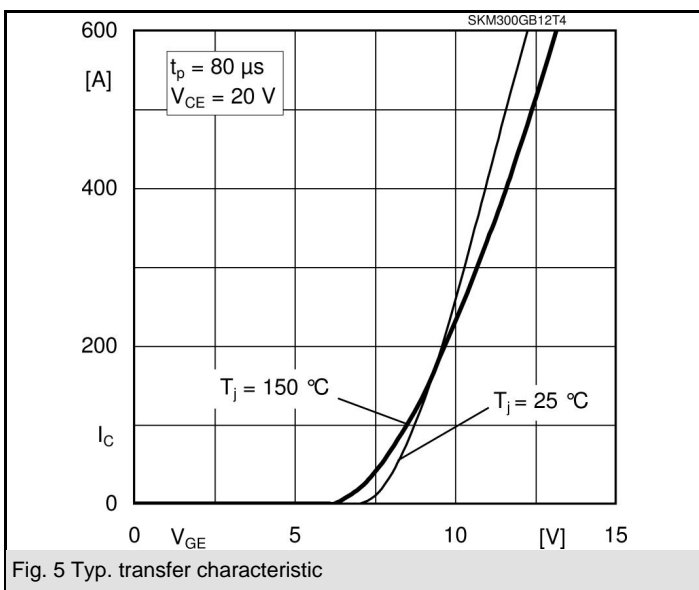
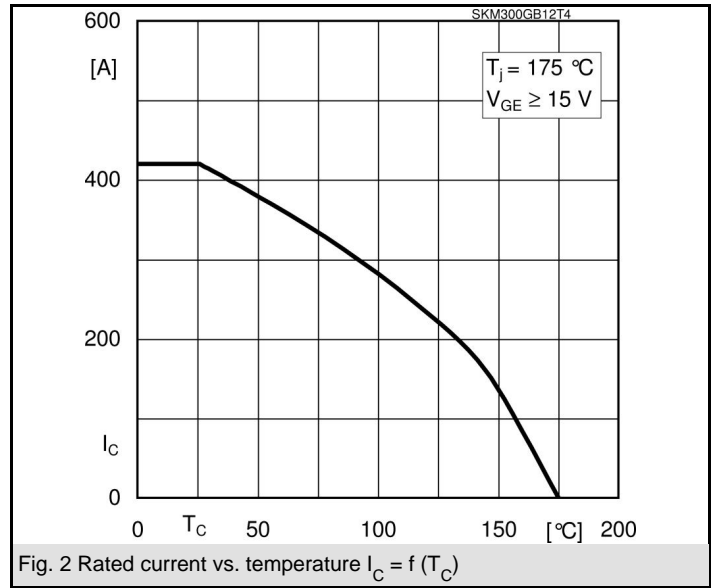
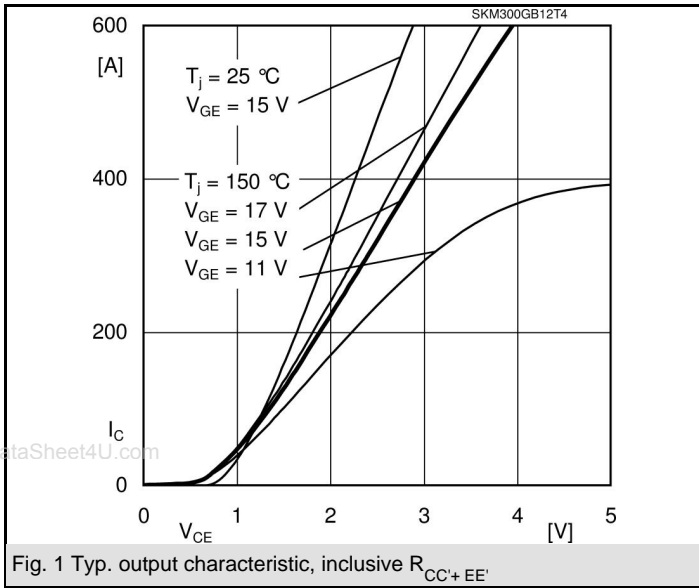
Characteristics			min.	typ.	max.	Units
Symbol	Conditions					
Inverse Diode						
$V_F = V_{EC}$	$I_{Fnom} = 300 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$		2,2	2,5	V
		$T_j = 150^\circ\text{C}_{chiplev.}$		2,1	2,45	V
V_{F0}		$T_j = 25^\circ\text{C}$		1,3	1,5	V
		$T_j = 150^\circ\text{C}$		0,9	1,1	V
r_F		$T_j = 25^\circ\text{C}$		3	3,33	mΩ
		$T_j = 150^\circ\text{C}$		4	4,5	mΩ
I_{RRM} Q_{rr} E_{rr}	$I_{Fnom} = 300 \text{ A}$	$T_j = 150^\circ\text{C}$		22,5		A μC mJ
$R_{th(j-c)}$	per diode				0,17	K/W
Freewheeling Diode						
$V_F = V_{EC}$	$I_{Fnom} = \text{A}; V_{GE} = \text{V}$	$T_j = ^\circ\text{C}_{chiplev.}$				V
V_{F0}		$T_j = ^\circ\text{C}$				V
r_F		$T_j = ^\circ\text{C}$				V
I_{RRM} Q_{rr} E_{rr}	$I_{Fnom} = \text{A}$	$T_j = ^\circ\text{C}$				A μC mJ
	per diode					K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$			0,35	mΩ
		$T_{case} = 125^\circ\text{C}$			0,5	mΩ
$R_{th(c-s)}$	per module			0,02	0,038	K/W
M_s	to heat sink M6			3	5	Nm
M_t	to terminals M6			2,5	5	Nm
w					325	g

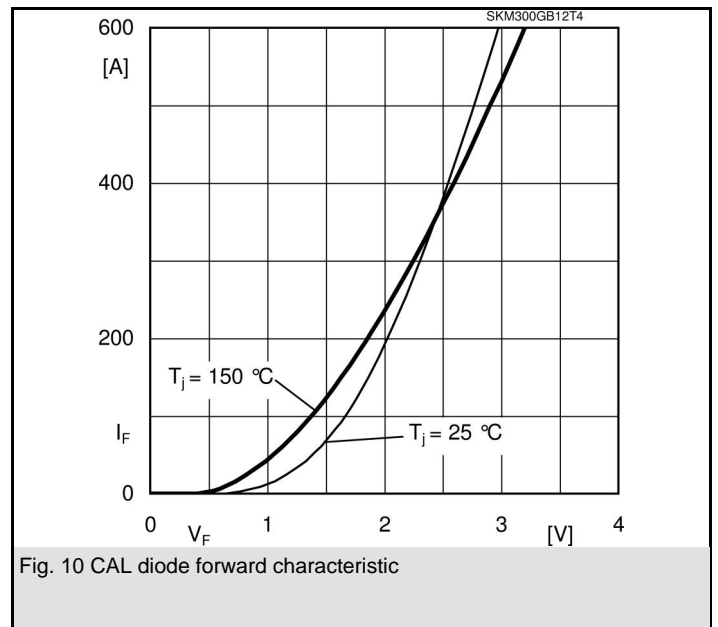
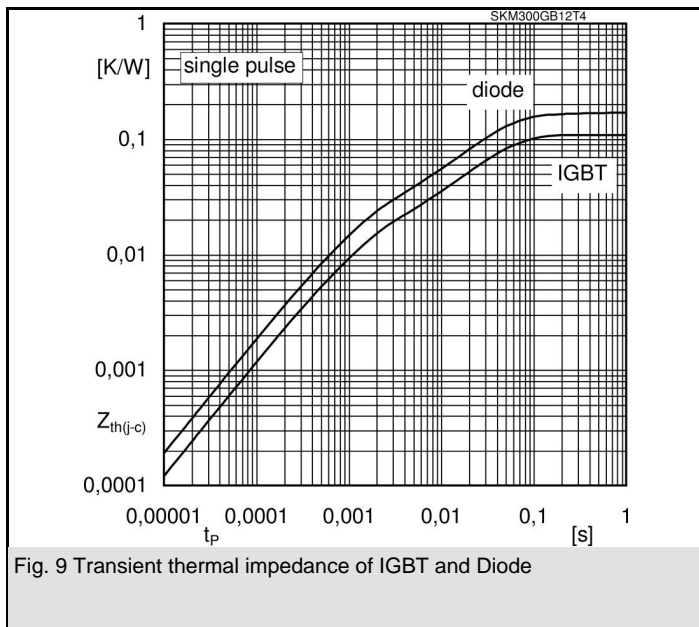
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



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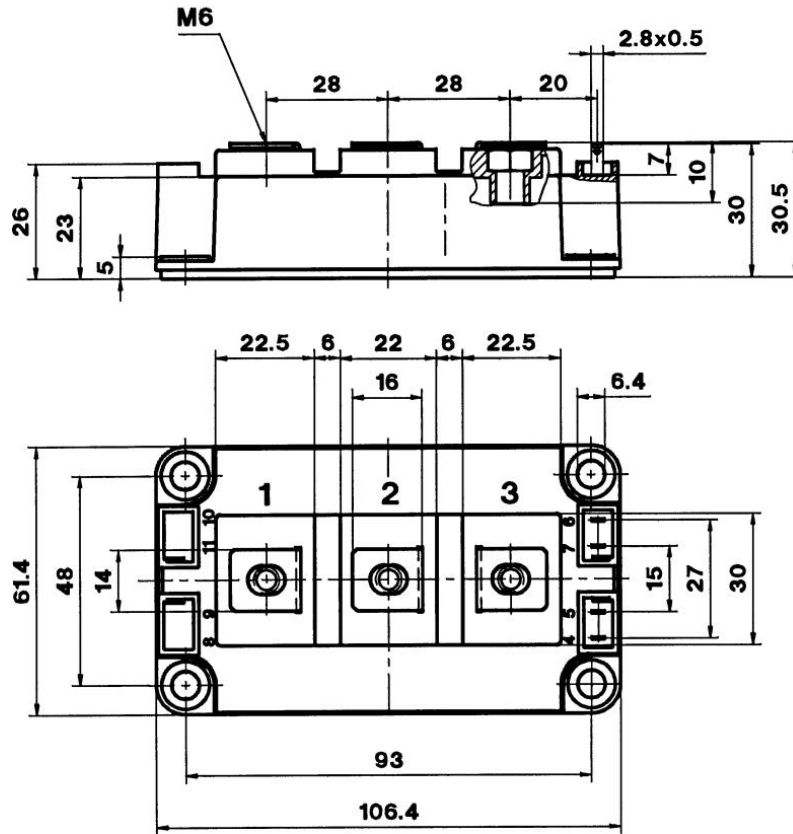


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UL recognized file

CASED56

no. E 63 532



Case D56

